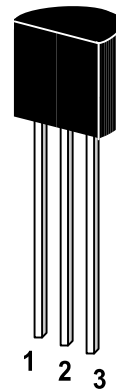


ST 2SC3203

NPN Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

The transistor is subdivided into two groups, O and Y
and according to its DC current gain.

On special request, these transistors can be
manufactured in different pin configurations.



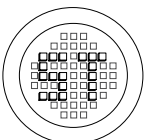
1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	35	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	800	mA
Emitter Current	I_E	-800	mA
Power Dissipation	P_{tot}	600	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^\circ\text{C}$

G S P FORM A IS AVAILABLE



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РАДИОТЕХ-ТРЕЙД

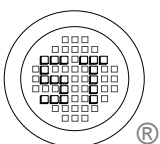
Тел.: (495) 795-0805
Факс: (495) 234-1603
Эл. почта: info@rct.ru
Веб: www.rct.ru

ST 2SC3203

Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

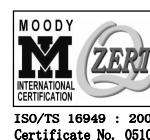
	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE}=1\text{V}$, $I_C=100\text{mA}$ Current Gain Group O Y	h_{FE}	100	-	200	-
	h_{FE}	160	-	320	-
	h_{FE}	35	-	-	-
at $V_{CE}=1\text{V}$, $I_C=700\text{mA}$					
Collector Cutoff Current at $V_{CB}=35\text{V}$	I_{CBO}	-	-	0.1	μA
Emitter Cutoff Current at $V_{EB}=5\text{V}$	I_{EBO}	-	-	0.1	μA
Collector Emitter Saturation Voltage at $I_C=500\text{mA}$, $I_B=20\text{mA}$	$V_{CE(sat)}$	-	-	0.5	V
Transition Frequency at $V_{CE}=5\text{V}$, $I_C=10\text{mA}$	f_T	-	120	-	MHz
Base Emitter Voltage at $I_C=10\text{mA}$, $V_{CE}=1\text{V}$	V_{BE}	0.5	-	0.8	V
Collector Output Capacitance at $V_{CB}=10\text{V}$, $f=1\text{MHz}$	C_{OB}	-	13	-	pF
Collector Emitter Breakdown Voltage at $I_C=10\text{mA}$	V_{CEO}	30	-	-	V

G S P FORM A IS AVAILABLE



SEMTECH ELECTRONICS LTD.

(Subsidiary of Semtech International Holdings Limited, acompany listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001
Certificate No. 7116



ISO 9001 : 2000
Certificate No. 0508-1999-01-002-001

Dated : 07/12/2002